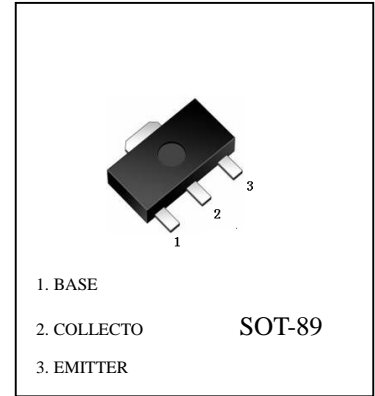


FEATURES

Complimentary to PXT8050

 Collector current: $I_C=1.5A$
MARKING: Y2

PXT8550 (PNP)

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1500	mA
Collector Power Dissipation	P_C	1000	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=0.1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20V, I_B=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	85		400	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$			-1	V
Base-emitter positive forward voltage	V_{BEF}	$I_B=-1A$			-1.	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA, f=30MHz$	100			MHz
output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			20	pF

CLASSIFICATION OF HFE

Rank	B	C	D	D1
Range	85-160	120-200	160-300	300-400

PXT8550 Typical Characteristics

